N-Channel 20-V (D-S) MOSFET

Key Features:

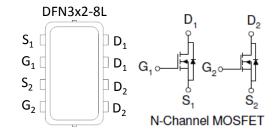
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

| Typical | App | lication | ıs: |
|----------------|-----|----------|-----|
| - , | | | |

- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

| PRODUCT SUMMARY | | | | |
|---------------------|-----------------------------|-------|--|--|
| V _{DS} (V) | $r_{DS(on)}(m\Omega)$ | I⊳(A) | | |
| 20 | 23 @ V _{GS} = 4.5V | 7.9 | | |
| 20 | $33 @ V_{GS} = 2.5V$ | 6.6 | | |





| ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED) | | | | | | |
|---|--------------------|--------------------|----------------|------------|-------|--|
| Parameter | | | Symbol | Limit | Units | |
| Drain-Source Voltage | | | V_{DS} | 20 | V | |
| Gate-Source Voltage | | | | ±8 | V | |
| Continuous Brain Commental | | ₄=25°C | ı | 7.9 | | |
| Continuous Drain Current ^a | T | ₄ =70°C | I _D | 6.4 | Α | |
| Pulsed Drain Current ^b | | | | 30 | | |
| Continuous Source Current (Diode Conduction) a | Is | 2.8 | Α | | | |
| Devices Discipation a | | ₄ =25°C | P _D | 2.1 | W | |
| Power Dissipation ^a | T _A =70 | | гD | 1.3 | VV | |
| Operating Junction and Storage Temperature Range | | | | -55 to 150 | °C | |

| THERMAL RESISTANCE RATINGS | | | | | | | |
|--|--------------|-----------------|---------|-------|--|--|--|
| Parameter | | Symbol | Maximum | Units | | | |
| Maximum Junction-to-Ambient ^a | t <= 10 sec | $R_{\theta JA}$ | 60 | °C/W | | | |
| Maximum Junction-to-Ambient | Steady State | IXOJA | 110 | | | | |

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

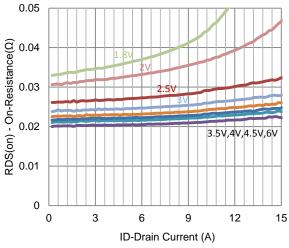
| Parameter | Symbol | Test Conditions | Min | Тур | Max | Unit | | |
|---------------------------------|---------------------|--|-----|------|------|-------|--|--|
| Static | | | | | | | | |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$ | 1 | | | V | | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$ | | | ±100 | nA | | |
| Zero Gate Voltage Drain Current | lana | $V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$ | | | 1 uA | | | |
| Zero Gate Voltage Brain Gurrent | I _{DSS} | $V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$ | 25 | | u/\ | | | |
| On-State Drain Current | $I_{D(on)}$ | $V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$ | 15 | | | Α | | |
| Drain-Source On-Resistance | r | $V_{GS} = 4.5 \text{ V}, I_D = 6.3 \text{ A}$ | 23 | | mΩ | | | |
| Dialii-30dice Oil-Resistance | r _{DS(on)} | $V_{GS} = 2.5 \text{ V}, I_D = 5.3 \text{ A}$ | | | 33 | 11122 | | |
| Forward Transconductance | g _{fs} | $V_{DS} = 10 \text{ V}, I_{D} = 6.3 \text{ A}$ | | 15 | | S | | |
| Diode Forward Voltage | V_{SD} | $I_{S} = 1.4 \text{ A}, V_{GS} = 0 \text{ V}$ | | 0.72 | | V | | |
| | | Dynamic | | | | | | |
| Total Gate Charge | Q_g | $V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V},$ | | 7 | | | | |
| Gate-Source Charge | Q_{gs} | $I_{DS} = 10 \text{ V}, \text{ V}_{GS} = 4.3 \text{ V},$ $I_{D} = 6.3 \text{ A}$ | | 1.2 | | nC | | |
| Gate-Drain Charge | Q_gd | 1D = 0.5 A | | 2.0 | | | | |
| Turn-On Delay Time | t _{d(on)} | $V_{DS} = 10 \text{ V}, R_{L} = 1.6 \Omega,$ | | 8 | | | | |
| Rise Time | t _r | $I_{DS} = 10 \text{ V}, K_L - 1.0 \Omega,$ $I_D = 6.3 \text{ A},$ | | 12 | | ne | | |
| Turn-Off Delay Time | $t_{d(off)}$ | $V_{GEN} = 4.5 \text{ V}, R_{GEN} = 6 \Omega$ | | 40 | | ns | | |
| Fall Time | t _f | V GEN - 4.5 V, T GEN - 0 12 | | 8 | | | | |
| Input Capacitance | C _{iss} | | | 581 | | | | |
| Output Capacitance | C _{oss} | $V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ | | 67 | | pF | | |
| Reverse Transfer Capacitance | C_{rss} | | | 65 | | | | |

Notes

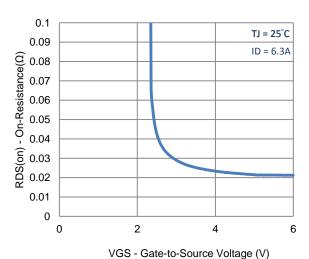
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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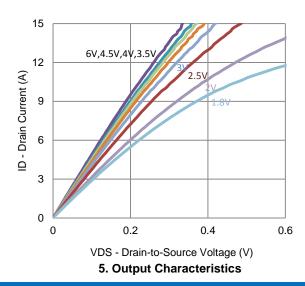
Typical Electrical Characteristics

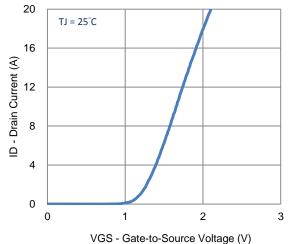


1. On-Resistance vs. Drain Current

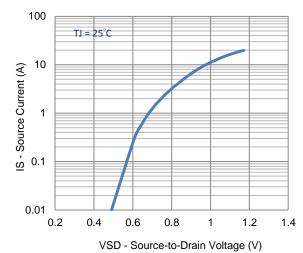


3. On-Resistance vs. Gate-to-Source Voltage

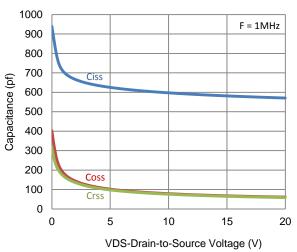




2. Transfer Characteristics

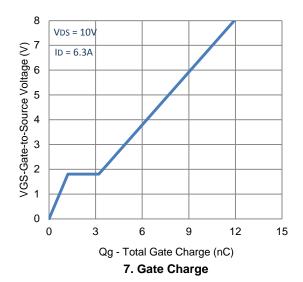


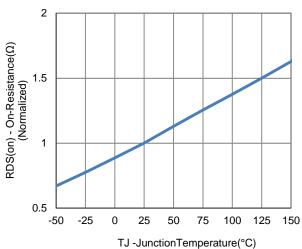
4. Drain-to-Source Forward Voltage



6. Capacitance

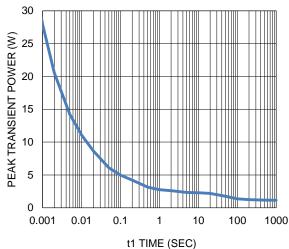
Typical Electrical Characteristics





100 10 ID Current (A) 1 1 SEC 10 SEC 100 SEC 0.1

8. Normalized On-Resistance Vs **Junction Temperature**

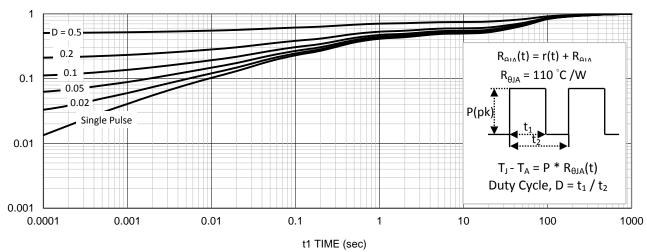


VDS Drain to Source Voltage (V) 9. Safe Operating Area

10

100

10. Single Pulse Maximum Power Dissipation

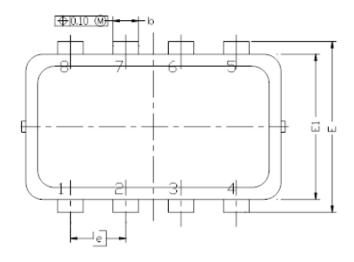


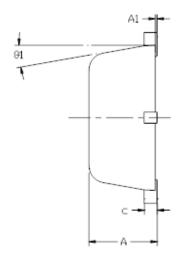
11. Normalized Thermal Transient Junction to Ambient

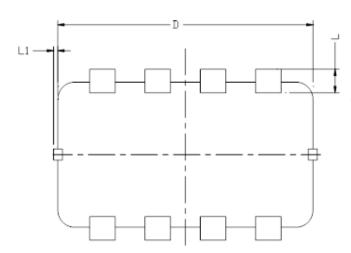
0.01

0.1

Package Information







| DIM. | MILLIMETERS | | | INCHES | | |
|--------|-------------|-------|-------|-----------|--------|--------|
| יואדתי | MIN | NDM | MAX | MIN NDM | | MAX |
| Α | 0.700 | 0.80 | 0.900 | 0.0276 | 0.0315 | 0.0354 |
| A1 | 0.00 | | 0.05 | 0.000 | 0.000 | |
| b | 0.24 | 0.30 | 0.35 | 0.009 | 0.012 | 0.014 |
| С | 0.08 | 0.152 | 0.25 | 0.003 | 0.006 | 0.010 |
| D | 3.00 BSC | | | 0.118 BSC | | |
| E | 2.00 B2C | | | 0.079 BSC | | |
| E1 | 1.70 BSC | | | 0.067 BSC | | |
| е | 0.65 BSC | | | 0.026 BSC | | |
| L | 0.20 | 0.275 | 0,400 | 0.008 | 0.011 | 0.0157 |
| L1 | 0 | | 0.100 | 0 | | 0.004 |
| 81 | 0. | 10° | 12° | 0° 10° | | 12° |

Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Tie Bar Burrs, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.
- 4. The Package Top May Be Smaller Than The Package Bottom.